

MA2C700, MA2C700A

Silicon epitaxial planar type

For ordinary wave detection

For super high speed switching

■ Features

- Low forward rise voltage (V_F) and satisfactory wave detection efficiency (η)
- Small temperature coefficient of forward characteristic
- Extremely low reverse current I_R
- DO-34(DHD) envelope, allowing to insert to a 5 mm pitch hole

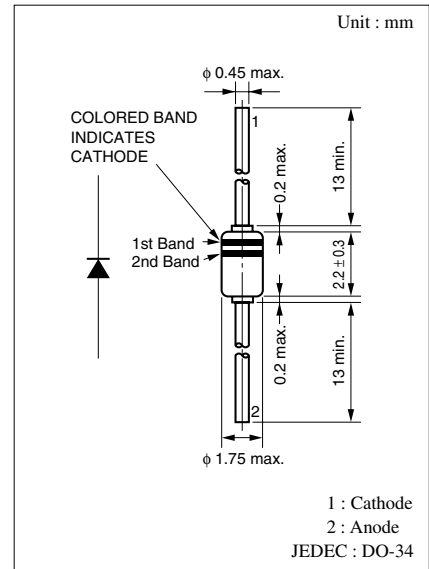
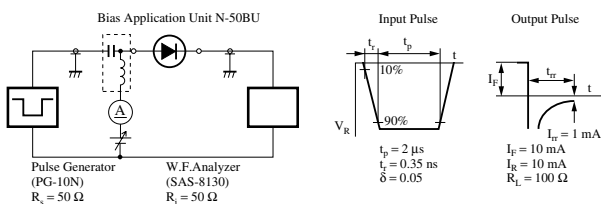
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	MA2C700	15	V
	MA2C700A	30	
Peak reverse voltage	MA2C700	15	V
	MA2C700A	30	
Peak forward current	I_{FM}	150	mA
Forward current (DC)	I_F	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	MA2C700	$V_R = 15\text{ V}$			100	nA
	MA2C700A	$V_R = 30\text{ V}$			150	nA
Forward voltage (DC)	V_{F1}	$I_F = 1\text{ mA}$			0.4	V
	V_{F2}	$I_F = 30\text{ mA}$			1	V
Terminal capacitance	C_t	$V_R = 1\text{ V}, f = 1\text{ MHz}$		1.3		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 10\text{ mA}$ $I_{rr} = 1\text{ mA}, R_L = 100\ \Omega$		1		ns
Detection efficiency	η	$V_{in} = 3\text{ V}_{(peak)}, f = 30\text{ MHz}$ $R_L = 3.9\text{ k}\Omega, C_L = 10\text{ pF}$		60		%

- Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment
2. Rated input/output frequency: 2 000 MHz
3. *: t_{rr} measuring instrument

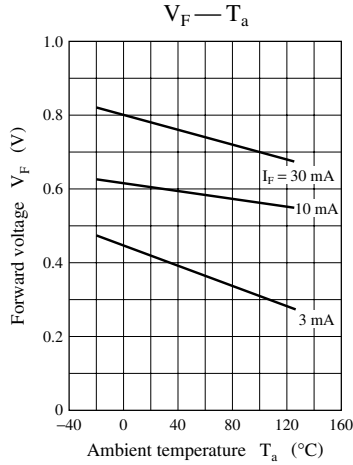
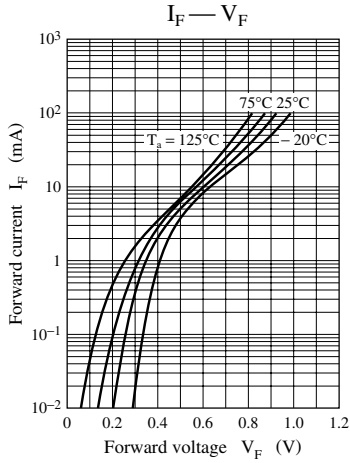


1 : Cathode
2 : Anode
JEDEC : DO-34

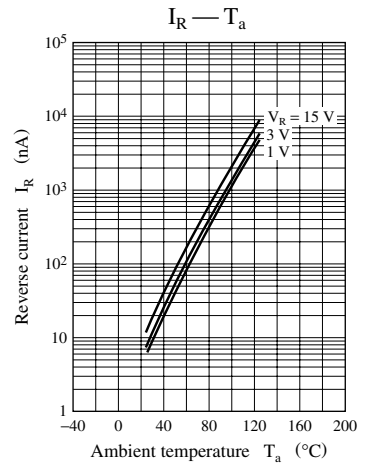
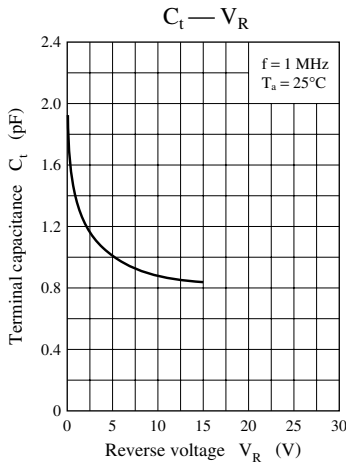
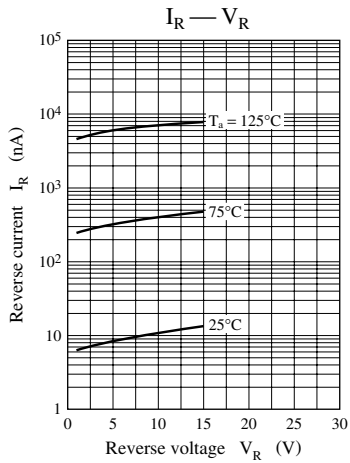
■ Cathode Indication

Type No.	MA2C700	MA2C700A
Color	1st Band: Silver	Silver
	2nd Band: —	Green

Common characteristics charts



Characteristics charts of MA2C700



Characteristics charts of MA2C700A

